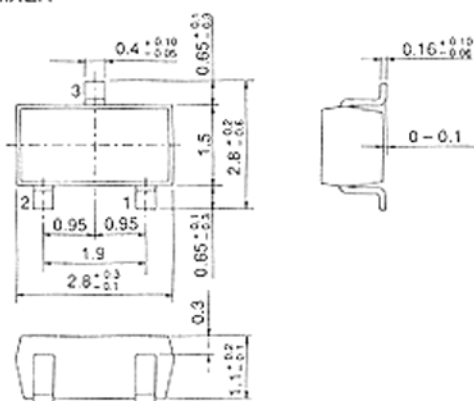


2SK197

SILICON N-CHANNEL JUNCTION FET

VHF AMPLIFIER, MIXER



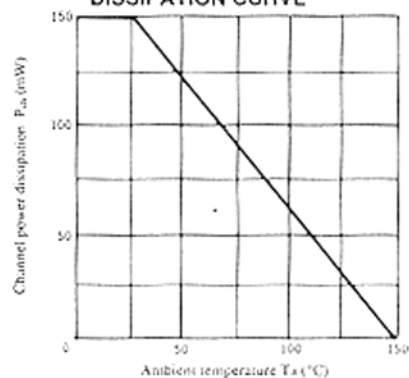
1. Gate
 2. Drain
 3. Source
- (Dimensions in mm)

(MPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SK197	Unit
Gate to drain voltage	V_{GDO}	-18	V
Drain current	I_D	20	mA
Gate current	I_G	10	mA
Channel power dissipation	P_{ch}	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

MAXIMUM CHANNEL POWER DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Gate to drain breakdown voltage	$V_{(BR)GDO}$	$I_G = -100\mu A, I_S = 0$	-18	—	—	V
Gate cutoff current	I_{GSS}	$V_{GS} = -0.5V, V_{DS} = 0$	—	—	-10	nA
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 10\mu A$	-0.3	—	-4.0	V
Drain current	I_{DSS}^*	$V_{DS} = 10V, V_{GS} = 0$	2	—	14	mA
Forward transfer admittance	$ y_{fs} $	$V_{DS} = 10V, V_{GS} = 0, f = 1kHz$	3.0	8.0	—	mS
Input capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	—	3.4	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	—	0.38	—	pF

* The 2SK197 is grouped by I_{DSS} as follows.

Grade	C	D	E
Mark	YC	YD	YE
I_{DSS}	2 to 5	3 to 7	6 to 14

■ See characteristic curves of 2SK55.